

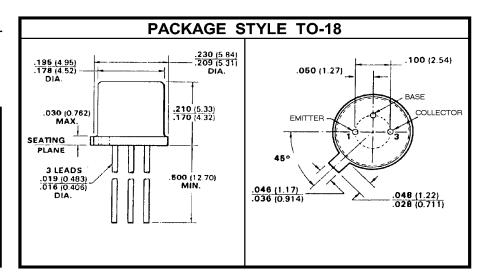
GERMANIUM PNP TRANSISTOR

DESCRIPTION:

The **2N2273** is Designed for General Purpose Switching, and VHF Amplifier Applications.

MAXIMUM RATINGS

Ic	100 mA					
V _{CE}	-15 V					
P _{DISS}	150 mW @ $T_A = 25$ $^{\circ}$ C					
TJ	-65 °C to +100 °C					
T _{STG}	-65 °C to +100 °C					
θ _{JC}	50 °C/W					



CHARACTERISTICS T_c = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CES}	I _C = 200 μA			-25			V
BV _{CBO}	I _C = 100 μA			-25			V
I _{CBO}	V _{CB} = -12 V					10	μА
BV _{EBO}	I _E = 100 μA			-0.5			٧
h _{FE}	$V_{CE} = -10 \text{ V}$ $I_C =$	1.0 mA		20		150	
f _t	$V_{CE} = -6.0 \text{ V}$ $I_{C} =$	1.0 mA f =	= 100 MHz	250			MHz
h _{fe}	$V_{CE} = -6.0 \text{ V}$ $I_{C} =$	1.0 mA f =	= 10 MHz	20		28	
C _{ob}	V _{CB} = -10 V	f =	= 1.0 MHz			3.5	pF
r _b	$V_{CE} = -10 \text{ V}$ $I_C =$	1.0 mA f =	= 250 MHz			250	Ohms
N _F	V_{CB} = -10 V I_{C} = R_{G} = 50 Ohms	1.0 mA f =	= 10 MHz			12	dB

ADVANCED SEMICONDUCTOR, INC.

REV. A

7525 ETHEL AVENUE • NORTH HOLLYWOOD, CA 91605 • (818) 982-1202 • TELEX: 18-2651 • FAX (818) 765-3004